Accelerated Molecular Dynamics

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Outline of the Lectures

- Motivation: Why Accelerated MD?
- Infrequent events and transition state theory
- Hyperdynamics
 - Basic concept

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- Trial applications
- Parallel Replica Dynamics
- Temperature Accelerated Dynamics

• Mathematical justification

• Application to thin film growth at experimental deposition rates





Conventional Molecular Dynamics Capabilities

- The maximum integration timestep in MD simulations is determined by the fastest motion in the system, typically vibrations.
- Typical molecular vibration frequencies range up to 3000 cm⁻¹ (period = 10 fs), and optical phonon frequencies are on the order of 10 THz (period = 100 fs).

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- A typical MD timestep is therefore on the order of 1 fs.
- Millions of timesteps only reach ns of simulation time.
- High-frequency stretch or bend modes can be frozen in molecular systems (e.g. SHAKE/RATTLE) or multiple timesteps used (e.g. r-RESPA), but the gain is typically only a factor of 2-3.

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Need for Accelerated Molecular Dynamics Methods

Many important problems lie beyond the timescales accessible to conventional MD, due to the infrequent surface or bulk diffusion mechanisms involved, including:

- Vapor-deposited thin film growth (metals and semiconductors) *especially heteroepitaxial layers*
- Stress-assisted diffusion of point defects, defect clusters, and dislocations
- Ion implantation or radiation damage annealing especially for complex crystal phases such as α-Pu



Vapor-deposited thin film growth

- Each deposition event lasts less than
 2 ps ideally suited for traditional MD.
- Experimental growth conditions are typically 1 monolayer per second or slower.



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- A delicate interplay of various diffusion barriers causes a nonmonotonic temperature dependence of the final surface roughness, from smooth layer-by-layer growth to rough 3D growth and back to layer-by-layer.
 - These activated processes, which determine the final morphology, occur on timescales far longer than that of traditional MD.

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Neutron/ion bombardment simulations

- Radiation damage or ion implantation simulations involve a rapid (ps) dissipation of the primary knock-on atom (PKA) kinetic energy, which is again well-suited to standard molecular dynamics.
- However, the typical α decay rate or ion flux is many orders of magnitude slower; for instance, ²³⁹Pu undergoes α decay with a half-life of 24,400 years. On average, each Pu atom is displaced from its lattice site once every 10 years, and during the same time period, 411 α-decays will occur for every million Pu atoms.



- kMC is extremely useful and has been applied to each of these problems, sometimes in combination with direct MD:
 - Simulations of energetic beam deposition: From picoseconds to seconds, J. Jacobsen, B.H. Cooper, and J.P. Sethna, Phys. Rev. B **58**, 15847 (1998).
 - Self-decay-induced damage production and micro-structure evolution in fcc metals: An atomic-scale computer simulation approach,
 T. Diaz de la Rubia *et al.*, J. Comp.-Aided Mat. Design 5, 243 (1998).
- kMC requires a prior knowledge (catalog) of all possible events.
- Even for one of the simplest systems submonolayer diffusion on a fcc(100) surface new diffusion mechanisms discovered during the 1990s raise questions about the completeness of kMC rate catalogs...



Unexpected events

Before 1990, most kMC catalogs for fcc(100) surface diffusion only contained a hop rate dependent on the local environment (occupancy of sites 1-10):



Slide 8 • A concerted exchange mechanism, only discovered in 1990, is *dominant* for some metals:



• The situation becomes nearly hopeless if we are interested in grain boundaries, strained systems (as in lattice-mismatched heteroepitaxial growth), or complex crystal structures...

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The low-temperature phase of plutonium (stable below 388 K at P = 0) resembles a distorted hcp lattice:



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• Predicting diffusion mechanisms for the α -phase structure is out of the question; even if they could all be enumerated, the resulting rate catalog may be prohibitively large.

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kMC with on-the-fly saddle searching

One possibility is to compute a kMC rate catalog whenever a new state is entered, using one of several saddle-finding methods:

• Mode-following techniques; particularly promising in this class is the dimer method, since no Hessian matrix is required:

A dimer method for finding saddle points on high dimensional potential surfaces using only first derivatives,

G. Henkelman and H. Jónsson, J. Chem. Phys. 111, 7010 (1999).

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• High-temperature sampling of possible escape routes

Can one ever be sure that all relevant mechanisms have been seen?

An ideal computational method for studying these phenomena would be MD-like, in that nothing about the possible escape paths needs to be specified in advance, only the interatomic potential (and not even that, in the case of *ab initio* MD).





Activation-Relaxation Technique (ART)

Event-Based Relaxation of Continuous Disordered Systems,

G.T. Barkema and N. Mousseau, Phys. Rev. Lett. **77**, 4358 (1996).

The activation-relaxation technique: an efficient algorithm for sampling energy landscapes,

G.T. Barkema and N. Mousseau, Comput. Mater. Sci. **20**, 285 (2001).



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• The activation step pushes the configuration up a valley towards a saddle point using the modified force

$$\mathbf{G} = \mathbf{F} - (1 + \alpha)(\mathbf{F} \cdot \mathbf{\Delta} \mathbf{x}) \mathbf{\Delta} \mathbf{x}$$

- Relaxation locates the basin on the other side of the saddle point.
- A Metropolis Monte Carlo probability may be used to accept or reject this event, or it may simply be added to a kMC rate catalog.

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Infrequent Event Systems

• All of these are examples of a more general class of problems, that of infrequent (or activated) event systems:



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- The system vibrates (and vibrates and vibrates...) in a many-dimensional potential basin the vast majority of the time.
- Occasionally but only very rarely it escapes through a dividing surface to a new potential basin.
- The objective is to accelerate these escapes *without* corrupting the relative escape probabilities for various exit pathways.

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• For infrequent event systems, assuming no correlated crossing events



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No dynamics required (although minimal dynamics in the dividing

- surface region can be used to improve the classical TST rate, or in various "quantum transition state theory" methods)
- Can we exploit TST to develop methods which do not require any knowledge of where dividing surfaces are?

Three Recent Methods for Infrequent Events

Hyperdynamics

A method for accelerating the molecular dynamics simulation of infrequent events, A.F. Voter, J. Chem. Phys. **106**, 4665 (1997).

Hyperdynamics: Accelerated Molecular Dynamics of Infrequent Events, A.F. Voter, Phys. Rev. Lett. **78**, 3908 (1997).

• Assumptions: infrequent events, TST

Slide 14 Parallel Replica Dynamics

Parallel replica method for dynamics of infrequent events, A.F. Voter, Phys. Rev. B **57**, R13985 (1998).

• Assumption: infrequent events

Temperature Accelerated Dynamics

Temperature-acclerated dynamics for simualation of infrequent events, M.R. Sørensen and A.F. Voter, J. Chem. Phys. **112**, 9599 (2000).

• Assumptions: infrequent events, *harmonic* TST, lower bound on preexponential factor





Hyperdynamics: Basic Approach

• Consider the Vineyard (harmonic TST) expression for the rate:





• The ratio of any two escape rates from state A only depends on the local properties at the saddles:

$$\frac{k_{A\to B}^{hTST}(T)}{k_{A\to C}^{hTST}(T)} = \prod_{i}^{3N-1} \left(\frac{\nu_{i}^{sad,AC}}{\nu_{i}^{sad,AB}}\right) e^{(E_{a}^{C} - E_{a}^{B})/k_{B}T}$$

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Hyperdynamics: Basic Approach

Therefore we are free to modify the basins however we like, as long as the saddle properties are unaffected. Add a positive bias potential ΔV_b(**r**) to the potential surface V(**r**) in the wells:



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- The TST rates increase by $e^{\Delta V_b(\mathbf{r}_A)/k_BT}$ (neglecting the prefactor)
- Since the escape rates are uniformly raised, a valid state-to-state sequence is obtained, but at an accelerated pace.
- In fact, harmonic TST is not required, only to assume TST is exact (implying no correlated crossing events), as we now show...

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Hyperdynamics: Mathematical Foundations

The transition state theory (TST) thermal rate constant is given by the canonical phase-space average $\langle \rangle_A$ of the flux through a dividing surface:

$$k_{A\to}^{TST} = \langle |v_A|\delta_A(\mathbf{r})\rangle_A$$

On a biased potential $V(\mathbf{r}) + \Delta V_b(\mathbf{r})$, using $\beta \equiv 1/k_B T$,

$$k_{A\to}^{TST} = \frac{\langle |v_A|\delta_A(\mathbf{r})e^{\beta\Delta V_b(\mathbf{r})}\rangle_{A_b}}{\langle e^{\beta\Delta V_b(\mathbf{r})}\rangle_{A_b}}$$

But since $\Delta V_b(\mathbf{r}) = 0$ whenever $\delta_A(\mathbf{r}) \neq 0$,

$$k_{A\to}^{TST} = \frac{\langle |v_A|\delta_A(\mathbf{r})\rangle_{A_b}}{\langle e^{\beta\Delta V_b(\mathbf{r})}\rangle_{A_b}}$$

So the TST escape rate on the biased surface is related to that on the original PES by $k_{A_b \to}^{TST} = k_{A \to}^{TST} \ \langle e^{\beta \Delta V_b(\mathbf{r})} \rangle_{A_b}$ I Illinois = Los Alamos

Hyperdynamics: Mathematical Foundations

The average escape time $\tau_{esc}^A = 1/k_{A\rightarrow}^{TST}$, so inverting the previous expression gives

$$\tau_{esc}^{A} = \tau_{esc}^{A_b} \langle e^{\beta \Delta V_b(\mathbf{r})} \rangle_{A_b}$$

Evaluating $\langle \rangle_{A_b}$ from a n_{tot} -step MD trajectory on the biased surface,

$$\tau_{esc}^{A} = \tau_{esc}^{A_b} \frac{1}{n_{tot}} \sum_{i}^{n_{tot}} e^{\beta \Delta V_b(\mathbf{r}(t_i))}$$

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Events are thus accelerated by the average "boost" factor

$$\frac{\tau^A_{esc}}{\tau^A_{esc}} = \frac{1}{n_{tot}} \sum_{i}^{n_{tot}} e^{\beta \Delta V_b(\mathbf{r}(t_i))}$$

and we can simply run a hyperclock which advances by $\Delta t_{hyper} = \Delta t_{MD} \ e^{\beta \Delta V_b(\mathbf{r}_i)}$ each timestep.

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Consider the simplest possible V_b :



Simple bias potential for boosting molecular dynamics with the hyperdynamics scheme, M.M. Steiner, P.-A. Genilloud, and J.W. Wilkins, Phys. Rev. B **57**, 10236 (1998).

- Very cost effective (zero or negative overhead)
- Works well for low-dimensional systems (few atoms)
- Vanishing boost for large systems

Conclusion: may be useful for small first principles applications, but not for general many-dimensional systems (tens of atoms)

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Recognizing Saddle Points



The dividing (hyper-) surface has an intrinsically nonlocal definition. However, an *approximate* local criterion may be obtained by noting that:

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- At a first-order saddle point, the gradient g = 0 and the Hessian H has exactly one negative eigenvalue.
- The corresponding eigenvector C₁ points along the reaction coordinate, and is orthogonal to the dividing surface.
- Similarly, the ridge line has at least one negative eigenvalue, *ε*₁ < 0, and the gradient along C₁ is zero.

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- Along a ridge line, the lowest eigenvalue (*ϵ*₁) of the Hessian is negative, and along its eigenvector (C₁), the gradient is zero.
- Therefore, a possible bias potential is one that turns on smoothly when either of these conditions is violated:

$$\Delta V_b(\mathbf{r}) = a\theta(\epsilon_1)\epsilon_1^2 + c(\mathbf{C}_1 \cdot \mathbf{g})^2,$$

Slide 21 where $\theta(x)$ is a step function (1 when x > 0 and 0 when x < 0) and g is the potential gradient, $g_i \equiv \partial V(\mathbf{r}) / \partial x_i$.

Alternatively, a bias potential which exactly "fills in" a cosine potential V(x) = (h/2) cos (x/d) with barrier height h and period 2πd may be used:

$$\Delta V_b^{cos}(x) = \frac{h}{2} \left[1 + \frac{\epsilon_1}{(\epsilon_1^2 + (\mathbf{C}_1 \cdot \mathbf{g})^2/d^2)^{1/2}} \right]$$

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Extracting a relevant "boosted" time

• Each timestep we advance the t_{hyper} clock by an amount

$$\Delta t_{hyper} = \Delta t_{MD} \exp\left(\Delta V_b(\mathbf{r}_i)/k_BT\right)$$

• The resulting t_{hyper} evolution is highly nonlinear:





2-D model with various bias potentials

- Exponential boost factor is apparent:
- In the lab, you can experiment with different bias potential choices
- More complex variants by adding another cos term and/or additional "y-like" degrees of freedom

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Embedded Atom Method (EAM) Potentials

- Pair potentials (e.g. Lennard-Jones) are unable to capture many-body effects in covalent species and metals
- EAM is based on density functional theory
- Used for metals, especially those with empty or filled d bands

$$E_{tot} = \sum_{i} F_i(\rho_i) + \frac{1}{2} \sum_{i \neq j} \phi_{ij}(R_{ij})$$

where

$$\rho_i = \sum_{j \neq i} \rho_j^a(R_{ij})$$

- F_i represents the embedding energy for each atom into a host electron gas due to neighboring atoms
- ϕ_{ij} is a core-core electrostatic (repulsive) pair interaction

Hessian-free bias potentials[†]

For large systems (100 or more atoms), setting up and diagonalizing the Hessian **H** becomes a serious bottleneck. Since only the lowest eigenvalue (or lowest few eigenvalues) is needed, iterative Lanczos-type methods can be used. Better yet is a bias potential which does not even require an explicit Hessian construction:

- The lowest eigenvalue ϵ_1 corresponds to the direction \mathbf{s}_1 which minimizes the second derivative $\partial^2 V(\mathbf{r})/\partial \mathbf{s}_1^2$.
- Express ϵ_1 as a numerical derivative,

$$\epsilon_1(\mathbf{s}_1) \simeq \frac{V(\mathbf{r} + \eta \mathbf{s}_1) + V(\mathbf{r} - \eta \mathbf{s}_1) - 2V(\mathbf{r})}{\eta^2}$$

Using steepest descent or conjugate gradient methods, vary the direction s₁ to minimize ε₁.

[†]A. F. Voter, Phys. Rev. Lett. **78**, 3908 (1997).

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In addition to ϵ_1 , we also need the gradient projection on its eigenvector, $g_{1p} \equiv \mathbf{C}_1 \cdot \mathbf{g}$ and its derivative. This is done in the same spirit:

 Numerically determine the lowest eigenvalues ε[±] for the modified Hessian H ± λgg[†] by minimizing

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$$\epsilon^{\pm}(\mathbf{s}) \simeq \frac{V(\mathbf{r}+\eta\mathbf{s}) + V(\mathbf{r}-\eta\mathbf{s}) - 2V(\mathbf{r})}{\eta^2} \pm \lambda \left[\frac{V(\mathbf{r}+\eta\mathbf{s}) + V(\mathbf{r}-\eta\mathbf{s})}{2\eta}\right]^2$$

• Combine to approximate
$$g_{1p}$$
 as $(g_{1p})^2 \simeq \frac{\epsilon^+ - \epsilon^-}{2\lambda}$

- Only a few dimer iterations are needed to converge ε[±] using s₁ as a first guess to s
- Gradient of g_{1p} has a simple form
- But numerical instabilities for small λ need to be investigated
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More on bias potentials...

This iterative N-scaling approach:

- only requires first derivatives of $V(\mathbf{r})$
- typically requires 20-50 force calls for EAM potentials

For numerical stability and other problems (e.g., $g_{1p} \rightarrow 0$) when the lowest two eigenvalues cross, an added eigenvalue repulsion term is useful:

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$$\Delta V_b^{\Delta \epsilon} = \begin{cases} a[1 - 3q^2 + 2q^3] & \text{if } \epsilon_2 - \epsilon_1 \leq \Delta \epsilon_c \\ 0 & \text{otherwise} \end{cases}$$

where $q \equiv (\epsilon_2 - \epsilon_1)/\Delta \epsilon_c$. By maintaining orthogonality of s_2 to the numerically determined s_1 , ϵ_2 can be computed in a similar manner as ϵ_1 .

The final bias potential is $\Delta V_b = \Delta V_b^{cos} + \Delta V_b^{\Delta \epsilon}$, with the ΔV_b^{cos} height h set to be somewhat less than the lowest anticipated barrier.

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An automatic procedure may also be used to set the bias strength h dynamically during a simulation in a "safe" manner:

If no event has occured after running dynamics for a time t, then we can put a lower bound on the lowest barrier E_a for escape from this state, using a typical prefactor ν₀ ≃ 10¹²:

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t < 1/ (fastest rate)

fastest rate $\simeq 10^{12} e^{-E_a^{min}/k_B T}$

- Therefore, $E_a^{min} > k_B T \ln (10^{12} t)$ and the bias potential strength h can be set to a value slightly below this value.
- Reset *h* = 0 (or some safe minimum value) and restart this procedure after each transition to safely ramp up the bias potential.



- Increasing the system size by adding spectator atoms has no effect on the performance (only making each MD step more expensive).
- The achievable boost drops as the number of "active" atoms in the system (i.e., the number of low-frequency eigenmodes) is increased, and it takes longer to converge the eigenvalues:



The Low-Barrier Problem

Often, a set of states may be connected by transitions with small activation energies, limiting the boost which could be achieved once a more stable configuration is reached via a higher- E_a mechanism:



This is still an unsolved problem for hyperdynamics!

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• Harness parallel or distributed processors to extend simulation time for infrequent event systems by independently exploring phase space



• When any processor detects a transition, sum the trajectory times from all processors, and restart all processors in the new state.

Detecting Transitions

• Do a periodic (say, every 2 ps) steepest descent or conjugate gradient minimization just long enough to ascertain whether the configuration has crossed to a different basin.



- Usually, only a few steps are required to say no transition has occured.
- Near saddle points, 100 steps may be needed.

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Parallel Replica Dynamics: Mathematical Foundations

- Assume only infrequent events having a first-order rate process, with a total escape rate equal to the sum of all n individual escape path rates: $k_{tot} = \sum_{i}^{n} k_{i}$.
- The escape-time probability distribution is $p(t) = k_{tot}e^{-k_{tot}t}$.
- If we run M replicas, we have Mn escape paths with a total escape rate Mk_{tot} , whose probability distribution function is

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$$p(t_1) = Mk_{tot}e^{-Mk_{tot}t_1}$$

where t_1 is the simulation time accumulated on any one processor.

• Rewrite this using $t_{sum} \equiv M t_1$:

$$p(t_{sum}) = \frac{1}{M} p\left(\frac{t_{sum}}{M}\right) = k_{tot} e^{-k_{tot}t_{sum}}$$

where the left equality comes from p(t/M)dt/M = p(t)dt.

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Parallel Replica Dynamics: Mathematical Foundations

• We therefore obtain the correct escape-time distribution,

$$p(t_{sum}) = k_{tot} \ e^{-k_{tot} t_{sum}}$$

• The same analysis is valid for inequivalent processors; M is replaced by a real-valued quantity (the sum of relative processor speeds), and the summed time becomes $t_{sum} = \sum_{i}^{M} t_{i}$.

- Only infrequent event dynamics was assumed; TST is not required.
- Recrossing or other correlated events are allowed to occur by continuing the dynamics on the processor which detected a transition for an additional time $\Delta t_{corr} \simeq 2$ ps.





Multiplicative speedups may be obtained by running accelerated MD trajectories on each replica, e.g. using hyperdynamics:



Cu/Cu(100) epitaxial growth

The combined parallel replica hyperdynamics has been demonstrated on epitaxial surface growth at experimental deposition rates:

- 100 K and 120 K
- 10 monolayers (ML) per second
- 1200 ASCI Red (333 MHz Pentium II) processors
- 24 hours wall-clock time
- 0.3 sec boosted simulation time (3 ML)

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Ramping of bias potential may have been overly aggressive...

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Other Applications of Parallel Replica Dynamics

- Since the only assumption is infrequent events, the parallel replica method has potential uses beyond those considered here (entropic bottlenecks, non-atomistic systems, ...)
- Folding@home: V.S. Pande Group (Stanford)
 - Some proteins are known to exhibit an exponential distribution of time-to-folding.
 - The fastest proteins fold on a μ s timescale
 - Use free energy monitoring to detect transition
 - Widely distributed and heterogeneous processors (like SETI@home)
- SurfaceDiffusion@home, anyone?



Temperature Accelerated Dynamics

Again, the basic concept is rather simple:

• Run a trajectory at an elevated temperature T_{high} , but reject all attempted transitions (more on how this is done in a bit...).

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- Extrapolate the high-temperature escape times $\{t_{i,high}\}$ to times $\{t_{i,low}\}$ at the lower temperature T_{low} , using the Arrhenius relationship and measured activation energies $\{E_a^i\}$.
- Accept the transition with the shortest $t_{i,low}$.

The key question is how long one needs to run the T_{high} simulation...





High-Temperature Sampling

• Vineyard (harmonic TST):

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$$k^{hTST}(T) = n_{path} \quad \frac{\prod_{i} \nu_i^{min}}{\prod_{i}^{3N-1} \nu_i^{sad}} \quad e^{-E_a/k_BT}$$

3N

- Competition between entropic prefactor and activation energy E_a
- High T will tend to favor pathways with soft ν_i^{sad} (e.g. A → B) over those with small barriers (e.g. A → C):



- Periodically save configurations as the trajectory proceeds
- When a transition is detected, find the two saved configurations which bracket the dividing surface

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- Use the nudged elastic band method (H. Jónsson *et al.*, 1998) to optimize the minimum energy path and locate the saddle point.
- Check that steepest descent in each direction leads to the right basins.

TAD: Mathematical Foundations

- Assume infrequent events with first-order kinetics, i.e. a probability distribution for each escape path *i* given by $p(t_i) = k_i e^{-k_i t}$.
- Assume harmonic TST, with an Arrhenius form $k_i = \nu_i e^{-E_a^i/k_BT}$.
- Finally, assume that the prefactors ν_i have a lower bound, ν_{min} .
- Run basin-constrained simulation at a high temperature T_{high} to obtain a sequence of waiting times $\{t_{i,high}\}$.

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• Extrapolate these to a sequence of low-temperature waiting times $\{t_{i,low}\}$ using the Arrhenius relationship:

$$\{t_{i,low}\} = \{t_{i,high}\} \exp\left[E_a^i(\beta_{low} - \beta_{high})\right]$$

where $\beta \equiv 1/k_B T$.

• The transition with the shortest $t_{i,low}$ is accepted and the T_{low} clock is advanced by this time.

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The Arrhenius view

 $k_i = \nu_i e^{-E_a^i/k_B T}$



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Synthetic kMC Mode for the Low Barrier Problem

- Keep cumulative history of states.
- When a fast process has been attempted a number of times, estimate the rate. Put the process in the *synthetic* class.
- Exclude synthetic transitions from the time-extrapolation scheme.
- Generate random escape times for synthetic processes from exponential distribution using estimated rate.



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TAD Example: 1/4 ML Cu/Cu(111) at 150 K[†]





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Recap: Comparison of Different Methods

Hyperdynamics

- assumes infrequent events, TST
- requires construction of a valid bias potential
- low barriers are a problem

Parallel Replica Dynamics

- only assumes infrequent events
- can be combined with hyperMD (done) or TAD (harder)
- full parallel efficiency if $\tau_{rxn}/n_{proc} \gg \tau_{dephase}, \tau_{corr}$

Temperature Accelerated Dynamics

- assumes infrequent events, harmonic TST, minimum prefactor
- synthetic (kMC) mode reduces low-barrier problem
- probably the most powerful of the three, given its assumptions



Application to Thin Film Growth



• Use embedded atom method (EAM) potentials for Cu, Ag, ...

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- Periodic boundary conditions in lateral directions
 - For each deposition event, select a random position above the surface and run ordinary MD for 2 ps
 - Use accelerated dynamics (hyper + parallel, TAD, ...) to follow activated processes between depositions (μsec to sec)
 - Study morphology, mechanisms, etc. as function of the deposition parameters (rate, temperature, impact energy, incidence angle, ...)

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Application to Thin Film Growth

- Homoepitaxial growth at temperatures up to 100 K have been demonstrated using hyper + parallel replica dynamics (TCG and AFV) at rates up to 10 monolayers per second, and using on-the-fly kinetic Monte Carlo with the dimer method by Henkelman and Jónsson at 1 monolayer per millisecond.
- Work is in progress with Francesco Montalenti (LANL) and James Sprague (NRL) using TAD at *experimental* deposition rates (e.g., one monolayer every 15 seconds) for Cu/Cu(100), Ag/Ag(100), and Ag/Cu(100).
 - All of these simulations exhibit a surprisingly large number of concerted, multiatom events which would be omitted from most (if not all) kinetic Monte Carlo rate catalogs.
 - Stay tuned...



Concerted Smoothing Events

-0.79 eV

Several multiatom concerted events seen during Cu/Cu(100) growth:

0.58 eV

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